

1.2V Drive Nch MOSFET

RUE002N05

Structure

Silicon N-channel MOSFET

Features

- 1) High speed switing.
- 2) Small package(EMT3).
- 3)Ultra low voltage drive(1.2V drive).

Application

Switching

Packaging specifications

	Dealtone	Tanina
	Package	Taping
Type	Code	TL
	Basic ordering unit (pieces)	3000
RUE002N05		0

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	50	V	
Gate-source voltage	V_{GSS}	±8	V	
Drain current	Continuous	I _D	±200	mA
	Pulsed	I _{DP} *1	±800	mA
Source current	Continuous	Is	125	mA
(Body Diode)	Pulsed	I _{SP} *1	800	mA
Power dissipation		P _D *2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

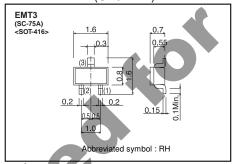
^{*1} Pw≤10µs, Duty cycle≤1%

Thermal resistance

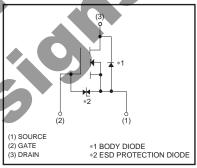
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C / W

^{*} Each terminal mounted on a recommended land.

• Dimensions (Unit : mm)



Inner circuit



^{*2} Each terminal mounted on a recommended land.

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●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	1	-	±10	μ A	$V_{GS}=\pm 8V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	٧	$I_D=1$ mA, $V_{GS}=0$ V
Zero gate voltage drain current	I _{DSS}	1	-	1	μ A	V_{DS} =50V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	-	1.0	٧	$V_{DS}=10V$, $I_{D}=1mA$
		1	1.6	2.2		$I_D = 200 \text{mA}, V_{GS} = 4.5 \text{V}$
Ctatia duain agunas an atata		1	1.7	2.4		$I_D = 200 \text{mA}, V_{GS} = 2.5 \text{V}$
Static drain-source on-state resistance	R _{DS (on)} *	1	1.9	2.7	Ω	I _D =100mA, V _{GS} =1.8V
100.014.1100		-	2.0	4.0		I _D =40mA, V _{GS} =1.5V
		-	2.4	7.2		I _D =20mA, V _{GS} =1.2V
Forward transfer admittance	I Y _{fs} I*	0.4	-	-	S	I _D =200mA, V _{DS} =10V
Input capacitance	C _{iss}	1	25	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	1	6	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	3	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	4	-	ns	$I_D=100$ mA, $V_D = 30$ V
Rise time	t _r *	-	6	-	ns	$V_{GS}=4.5V$
Turn-off delay time	t _{d(off)} *	-	15	-	ns	$R_L=300\Omega$
Fall time	t _f *	-	55	-	ns	$R_G=10\Omega$

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Forward voltage V_{SD}^* 1.2 V_{SD}^* - 1.2 V_{SD}^* Pulsed	Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
*Pulsed	Forward voltage	V _{SD} *	-	-	1.2	V	$I_s=200$ mA, $V_{GS}=0$ V
					36	<i>y</i>	

^{*}Pulsed

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Electrical characteristic curves

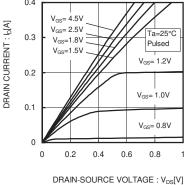
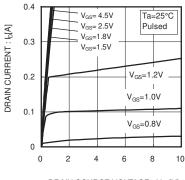
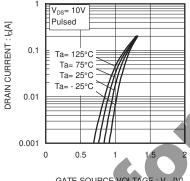


Fig.1 Typical Output Characteristics(I)



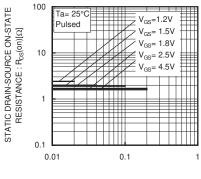
DRAIN-SOURCE VOLTAGE: VDS[V]

Fig.2 Typical Output Characteristics(II)



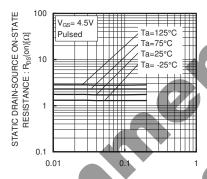
GATE-SOURCE VOLTAGE: V

Fig.3 Typical Transfer Characteristics



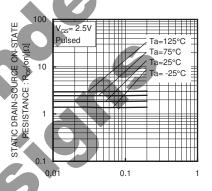
 $\mathsf{DRAIN}\text{-}\mathsf{CURRENT}:\mathsf{I}_\mathsf{D}[\mathsf{A}]$

Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)



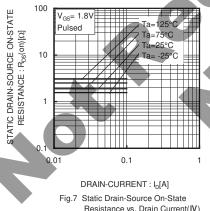
DRAIN-CURRENT : I_D[A]

Static Drain-Source On-State Resistance vs. Drain Current(II)



DRAIN-CURRENT : I_D[A]

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)



Resistance vs. Drain Current(IV)

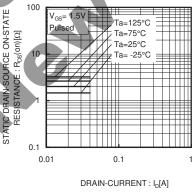


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

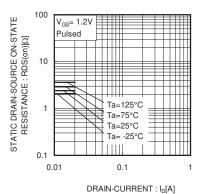


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI) RUE002N05 Data Sheet

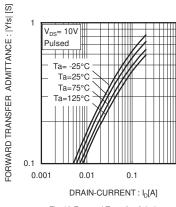


Fig.10 Forward Transfer Admittance vs. Drain Current

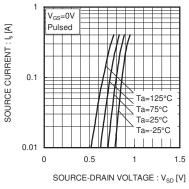


Fig.11 Reverse Drain Current vs. Sourse-Drain Voltage

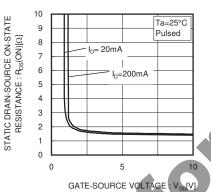
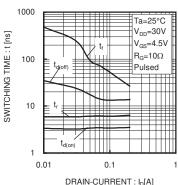
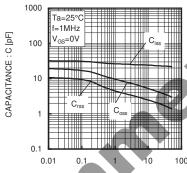


Fig.12 Static Drain-Source On-State
Resistance vs. Gate Source Voltage



DRAIN-CURRENT : I_D[A]
Fig.13 Switching Characteristics



DRAIN-SOURCE VOLTAGE : V_{DS}[V]
Fig.14 Typical Capacitance
vs. Drain-Source Voltage

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Measurement circuits

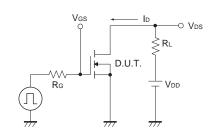


Fig.1-1 Switching time measurement circuit

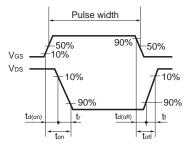


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.



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